

# PMPB10XNEA

20 V, N-channel Trench MOSFET

27 March 2018

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

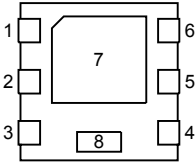
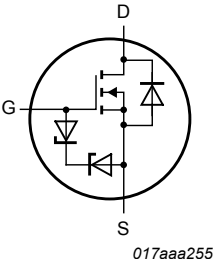
Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions                                                                  |     | Min | Typ | Max | Unit       |
|-------------------------------|----------------------------------|-----------------------------------------------------------------------------|-----|-----|-----|-----|------------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25\text{ }^{\circ}\text{C}$                                          |     | -   | -   | 20  | V          |
| $V_{GS}$                      | gate-source voltage              |                                                                             |     | -12 | -   | 12  | V          |
| $I_D$                         | drain current                    | $V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$               | [1] | -   | -   | 9   | A          |
| <b>Static characteristics</b> |                                  |                                                                             |     |     |     |     |            |
| $R_{DSon}$                    | drain-source on-state resistance | $V_{GS} = 4.5\text{ V}; I_D = 9\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$ |     | -   | 10  | 14  | m $\Omega$ |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                                                             | Graphic symbol                                                                      |
|-----|--------|-------------|------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | D      | drain       |  <p>Transparent top view<br/><b>DFN2020MD-6 (SOT1220)</b></p> |  |
| 2   | D      | drain       |                                                                                                                                                |                                                                                     |
| 3   | G      | gate        |                                                                                                                                                |                                                                                     |
| 4   | S      | source      |                                                                                                                                                |                                                                                     |
| 5   | D      | drain       |                                                                                                                                                |                                                                                     |
| 6   | D      | drain       |                                                                                                                                                |                                                                                     |
| 7   | D      | drain       |                                                                                                                                                |                                                                                     |
| 8   | S      | source      |                                                                                                                                                |                                                                                     |

6. Ordering information

Table 3. Ordering information

| Type number | Package     |                                                                                               |         |
|-------------|-------------|-----------------------------------------------------------------------------------------------|---------|
|             | Name        | Description                                                                                   | Version |
| PMPB10XNEA  | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB10XNEA  | 4E           |

## 8. Limiting values

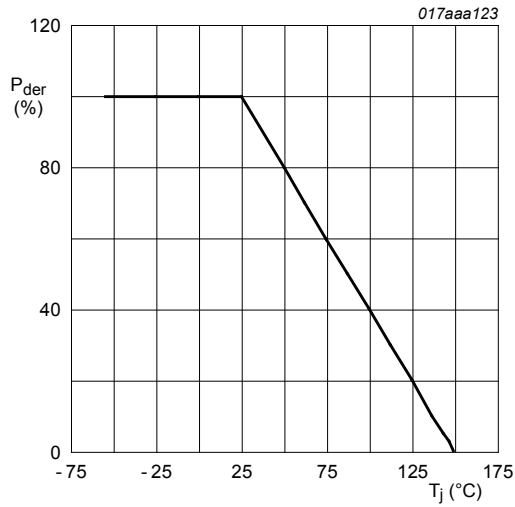
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions                                                                                            |     | Min | Max  | Unit               |
|-----------------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------|-----|-----|------|--------------------|
| $V_{DS}$                    | drain-source voltage                         | $T_j = 25\text{ }^{\circ}\text{C}$                                                                    |     | -   | 20   | V                  |
| $V_{GS}$                    | gate-source voltage                          |                                                                                                       |     | -12 | 12   | V                  |
| $I_D$                       | drain current                                | $V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$                                         | [1] | -   | 9    | A                  |
|                             |                                              | $V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$                                        | [1] | -   | 5.7  | A                  |
| $I_{DM}$                    | peak drain current                           | $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; single pulse; $t_p \leq 10\text{ }\mu\text{s}$               |     | -   | 36   | A                  |
| $P_{tot}$                   | total power dissipation                      | $T_{amb} = 25\text{ }^{\circ}\text{C}$                                                                | [1] | -   | 1.7  | W                  |
|                             |                                              | $T_{sp} = 25\text{ }^{\circ}\text{C}$                                                                 |     | -   | 12.5 | W                  |
| $T_j$                       | junction temperature                         |                                                                                                       |     | -55 | 150  | $^{\circ}\text{C}$ |
| $T_{amb}$                   | ambient temperature                          |                                                                                                       |     | -55 | 150  | $^{\circ}\text{C}$ |
| $T_{stg}$                   | storage temperature                          |                                                                                                       |     | -65 | 150  | $^{\circ}\text{C}$ |
| <b>Source-drain diode</b>   |                                              |                                                                                                       |     |     |      |                    |
| $I_S$                       | source current                               | $T_{amb} = 25\text{ }^{\circ}\text{C}$                                                                | [1] | -   | 2    | A                  |
| <b>ESD maximum rating</b>   |                                              |                                                                                                       |     |     |      |                    |
| $V_{ESD}$                   | electrostatic discharge voltage              | HBM                                                                                                   | [2] | -   | 1000 | V                  |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                       |     |     |      |                    |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $I_D = 2\text{ A}$ ; DUT in avalanche (unclamped) |     | -   | 21   | mJ                 |

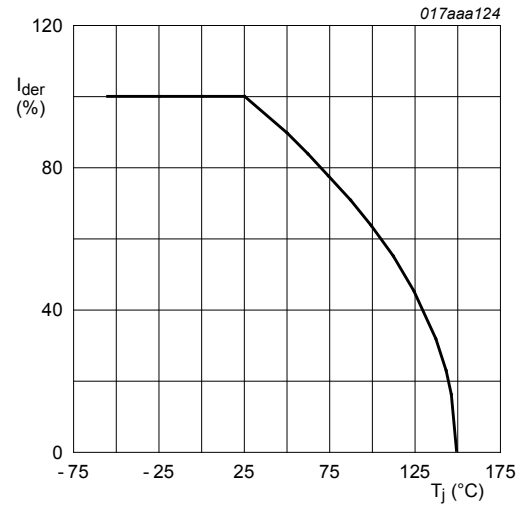
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $6\text{ cm}^2$ .

[2] Measured between all pins.



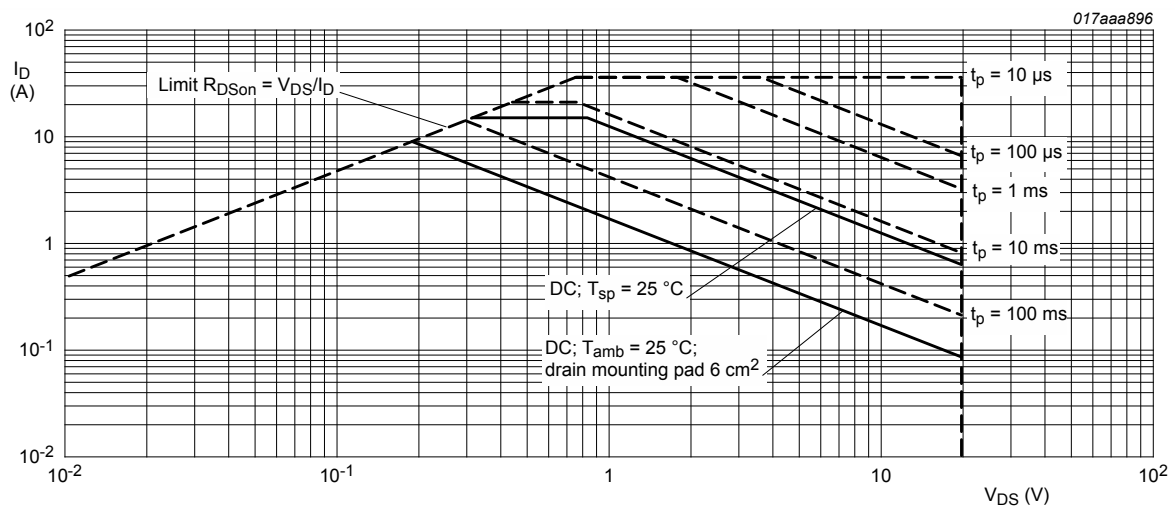
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

**Fig. 1.** Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$

**Fig. 2.** Normalized continuous drain current as a function of junction temperature



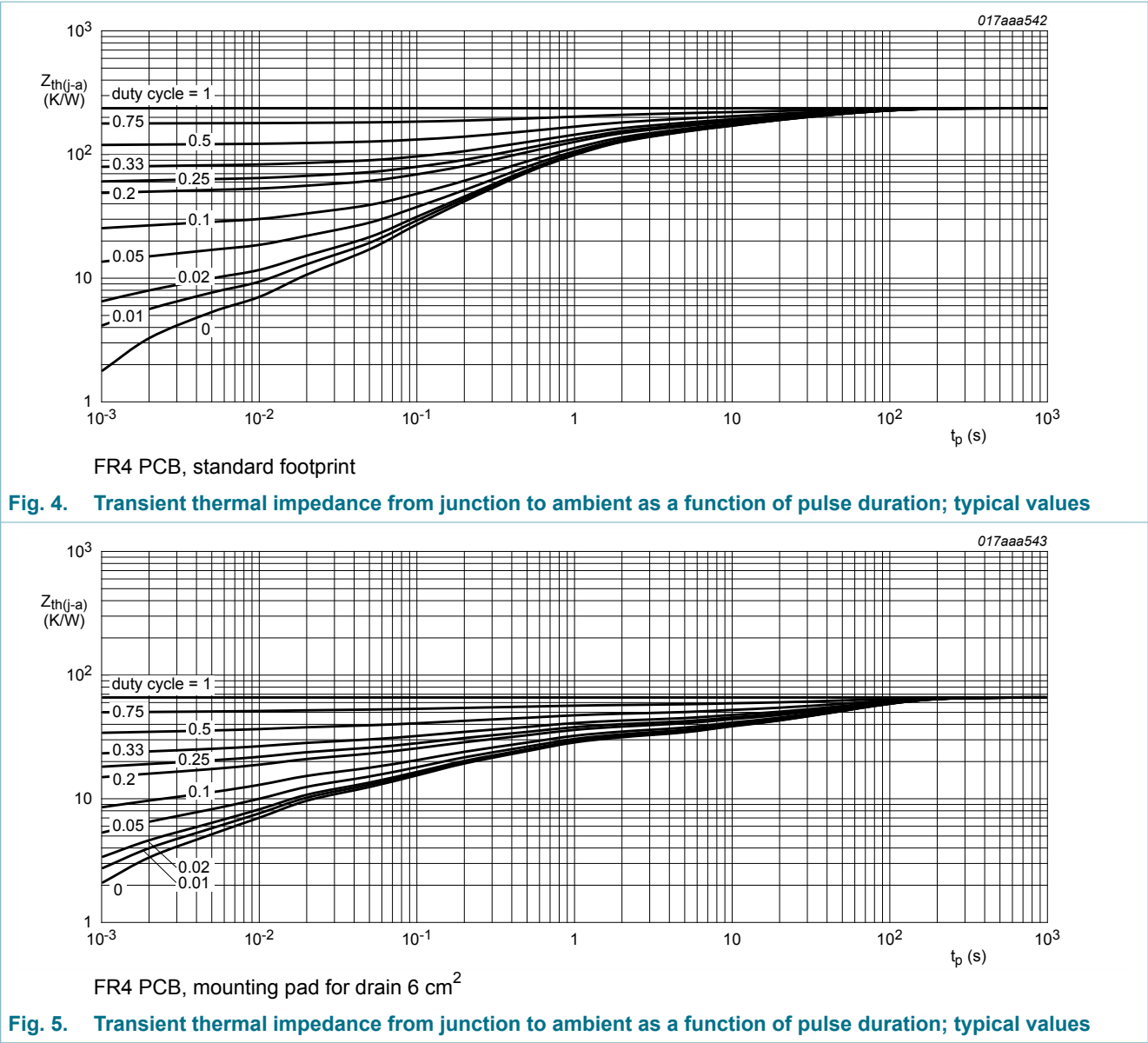
**Fig. 3.** Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions  |     | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | 235 | 270 | K/W  |
|                |                                                  |             | [2] | -   | 67  | 74  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             |     | -   | 5   | 10  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



## 10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                   |  | Min | Typ  | Max | Unit |
|-------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| Static characteristics  |                                  |                                                                                                                              |  |     |      |     |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                       |  | 20  | -    | -   | V    |
| V <sub>GSth</sub>       | gate-source threshold voltage    | I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C                                          |  | 0.4 | 0.65 | 0.9 | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                        |  | -   | -    | 1   | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                         |  | -   | -    | 10  | μA   |
|                         |                                  | V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                        |  | -   | -    | -10 | μA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C                                                        |  | -   | 10   | 14  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 150 °C                                                       |  | -   | 15   | 21  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                                        |  | -   | 12   | 18  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 3.7 A; T <sub>j</sub> = 25 °C                                                      |  | -   | 16   | 25  | mΩ   |
| g <sub>fs</sub>         | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C                                                         |  | -   | 60   | -   | S    |
| R <sub>G</sub>          | gate resistance                  | f = 1 MHz                                                                                                                    |  | -   | 2    | -   | Ω    |
| Dynamic characteristics |                                  |                                                                                                                              |  |     |      |     |      |
| Q <sub>G(tot)</sub>     | total gate charge                | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V; T <sub>j</sub> = 25 °C                                |  | -   | 23   | 34  | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                              |  | -   | 2.6  | -   | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                              |  | -   | 4.5  | -   | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                             |  | -   | 2175 | -   | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                              |  | -   | 235  | -   | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                              |  | -   | 205  | -   | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C     |  | -   | 13   | -   | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                              |  | -   | 35   | -   | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                              |  | -   | 54   | -   | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                              |  | -   | 50   | -   | ns   |
| Source-drain diode      |                                  |                                                                                                                              |  |     |      |     |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                          |  | -   | 0.6  | 1.2 | V    |
| t <sub>rr</sub>         | reverse recovery time            | I <sub>S</sub> = 2 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 10 V; T <sub>j</sub> = 25 °C |  | -   | 13   | -   | ns   |
| Q <sub>r</sub>          | recovered charge                 |                                                                                                                              |  | -   | 5    | -   | nC   |

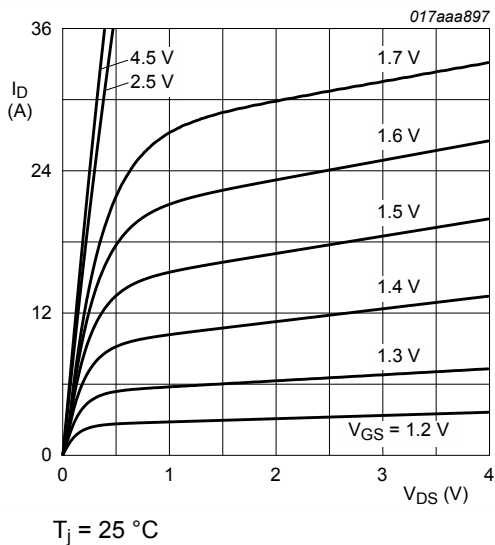


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

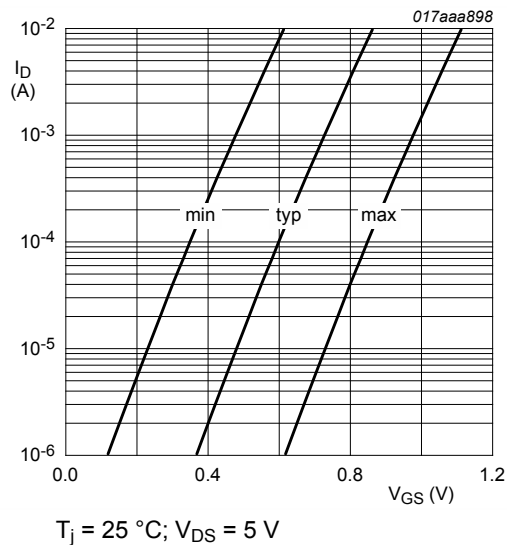


Fig. 7. Subthreshold drain current as a function of gate-source voltage

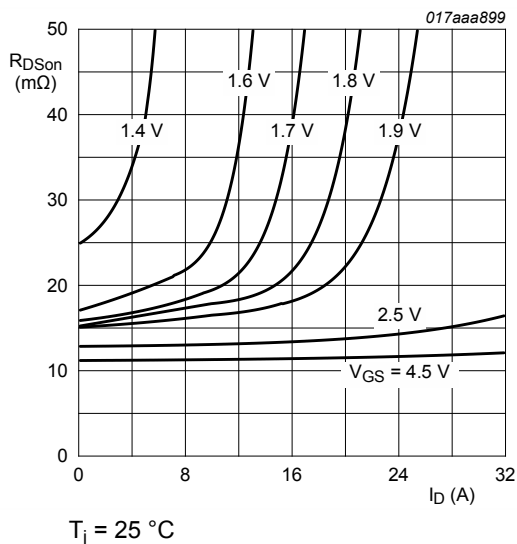


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

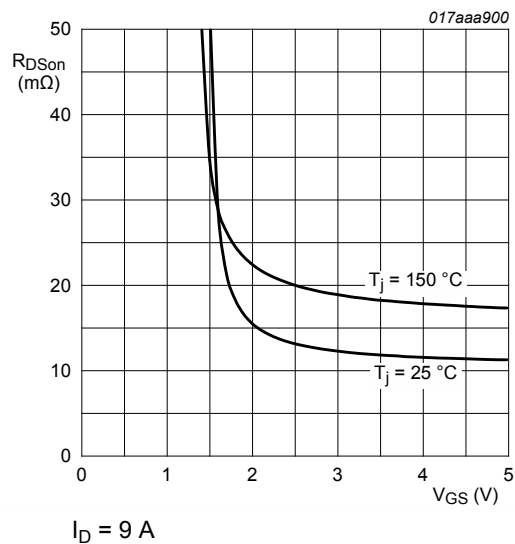


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

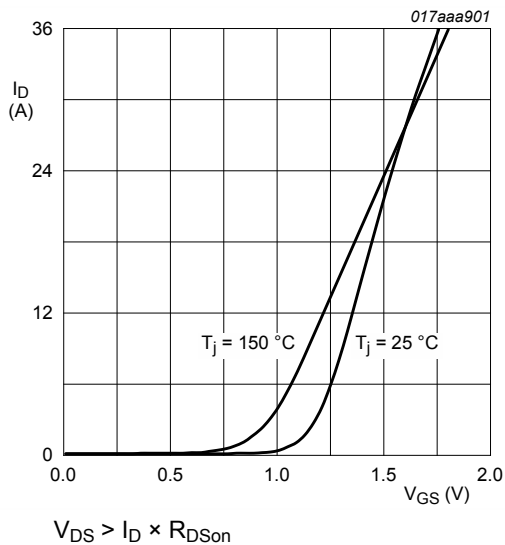


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

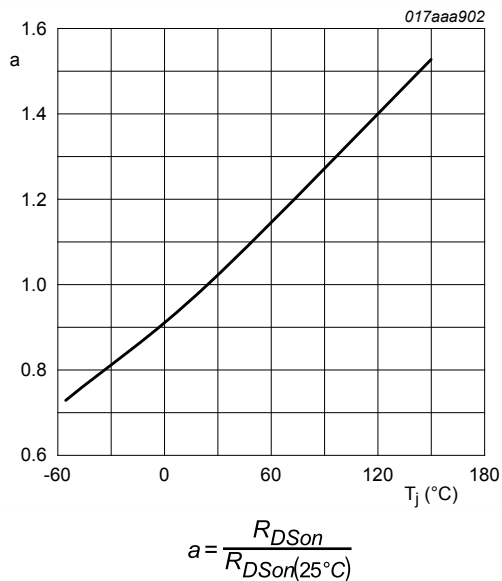


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

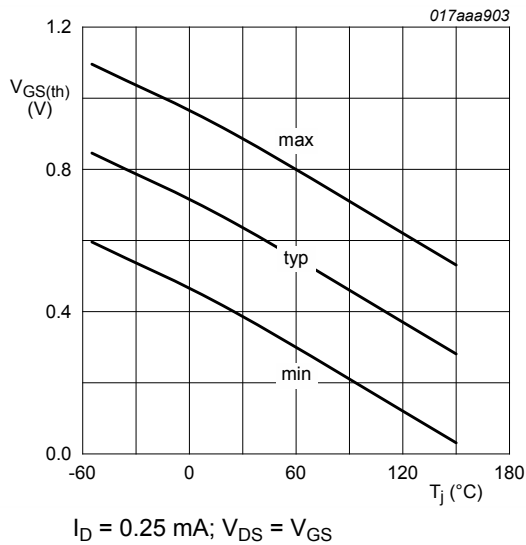


Fig. 12. Gate-source threshold voltage as a function of junction temperature

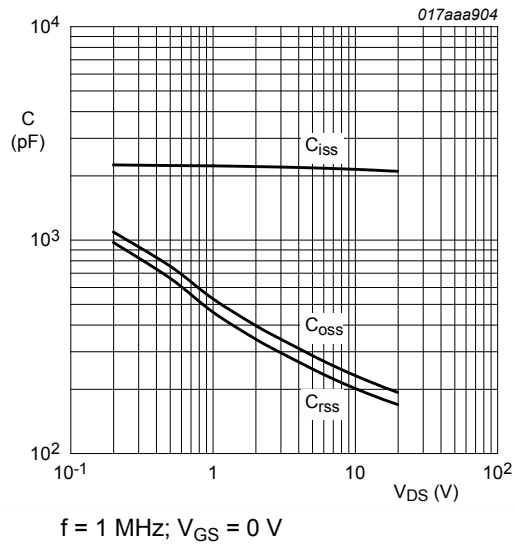


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



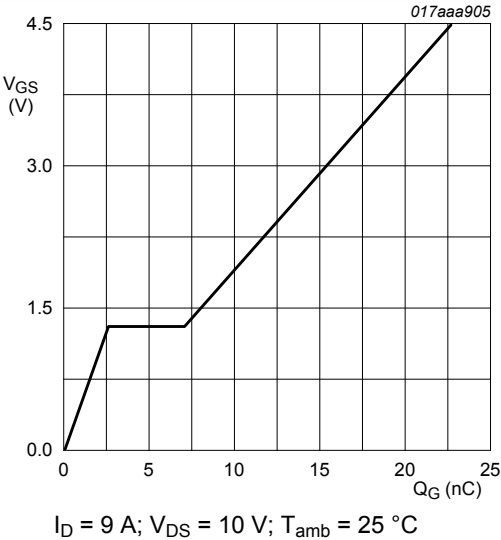


Fig. 14. Gate-source voltage as a function of gate charge; typical values

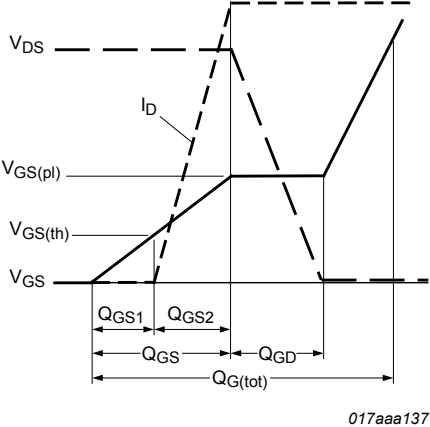


Fig. 15. MOSFET transistor: Gate charge waveform definitions

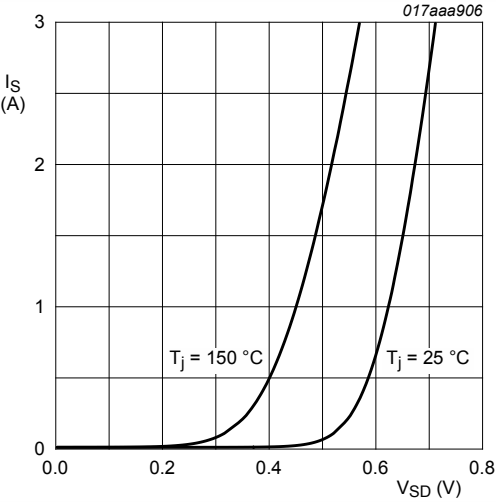


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

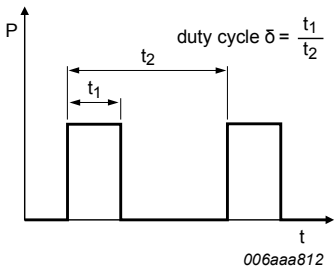


Fig. 17. Duty cycle definition

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

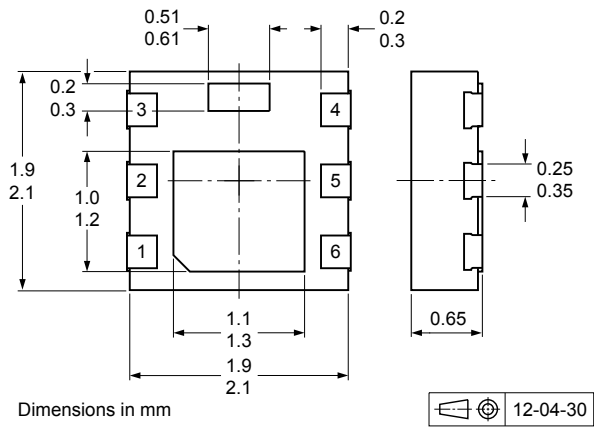
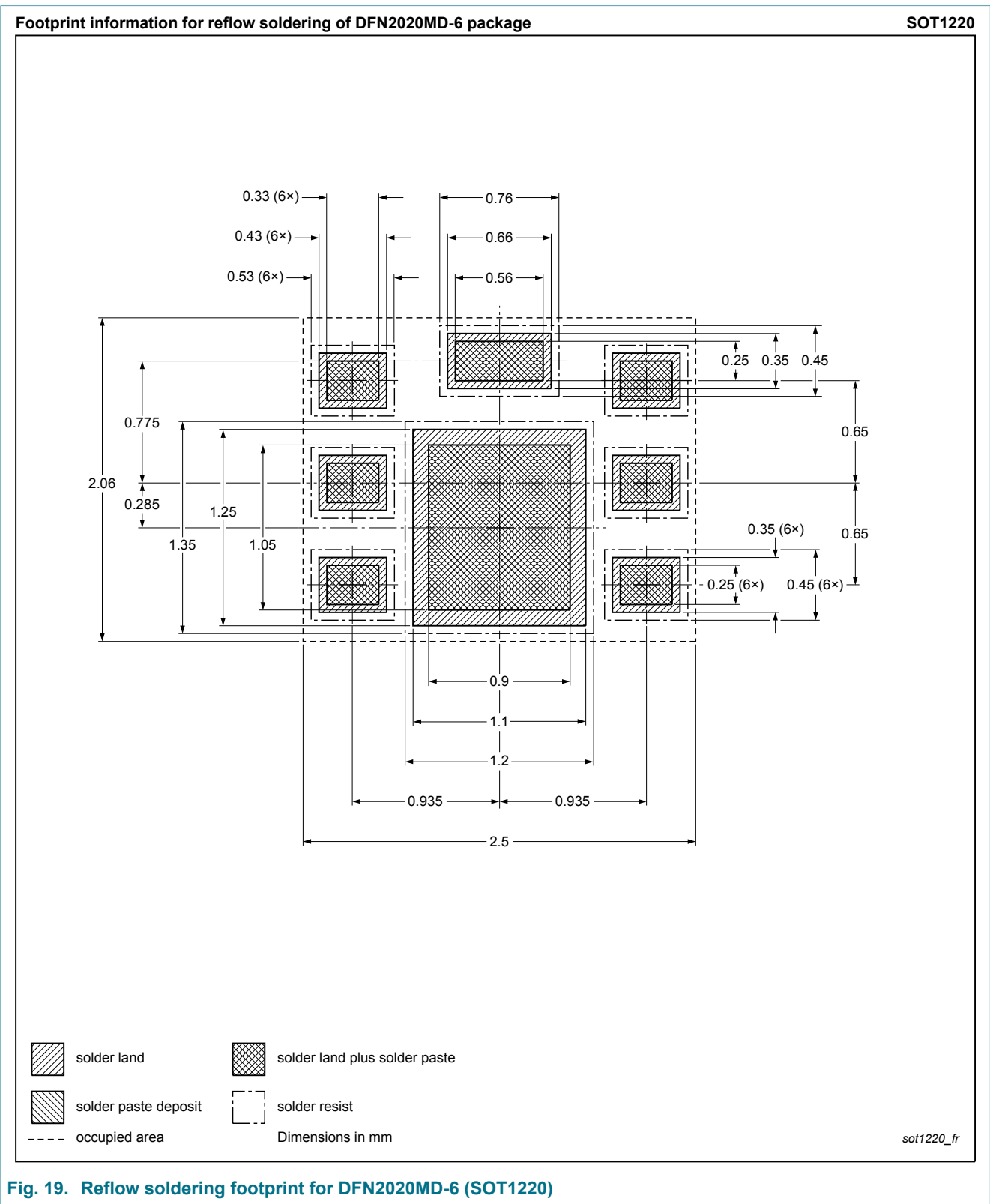


Fig. 18. Package outline DFN2020MD-6 (SOT1220)

13. Soldering



## 14. Revision history

Table 8. Revision history

| Data sheet ID  | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMPB10XNEA v.1 | 20180327     | Product data sheet | -             | -          |

## 15. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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Date of release: 27 March 2018

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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